Document Number: MHW9186A

Rev. 2, 5/2006

Gallium Arsenide CATV Amplifier Module

replacement. N suffix indicates RoHS compliant part.

Features

- Specified for 79-, 112- and 132-Channel Loading
- **Excellent Distortion Performance**
- Built-in Input Diode Protection
- GaAs FET Transistor Technology
- Unconditionally Stable Under All Load Conditions
- Improved Ruggedness

Applications

- CATV Systems Operating in the 40 to 870 MHz Frequency Range
- Input Stage Amplifier in Optical Nodes, Line Extenders and Trunk Distribution Amplifiers for CATV Systems
- Output Stage Amplifier on Applications Requiring Low Power Dissipation and High Output Performance

Replaced by MHW9186AN. There are no form, fit or function changes with this part

Driver Amplifier in Linear General Purpose Applications

Description

24 Vdc Supply, 40 to 870 MHz, CATV GaAs Forward Amplifier Module

MHW9186A

870 MHz **18.5 dB GAIN** 132-CHANNEL **GaAs CATV AMPLIFIER MODULE**



CASE 1302-01, STYLE 1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
RF Voltage Input (Single Tone)	V _{in}	+65	dBmV
DC Supply Voltage	V _{CC}	+26	Vdc
Operating Case Temperature Range	T _C	-20 to +100	°C
Storage Temperature Range	T _{stg}	-40 to +100	°C

Table 2. ESD Maximum Ratings

Rating	Input Value	Output Value	Unit
Surge Voltage per IEC 1000-4-5	300	300	V
Human Body Model per Mil. Std. 1686	2	2	kV

Table 3. Electrical Characteristics ($V_{CC} = 24 \text{ Vdc}$, $T_{C} = +30^{\circ}\text{C}$, 75 Ω system unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Frequency Range		BW	40	_	870	MHz
Power Gain	870 MHz	G _p	18	18.5	19.5	dB
Slope	40-870 MHz	S	0.1	0.6	1.2	dB
Gain Flatness (40-870 MHz, Peak-to	-Valley)	G _F	_	0.3	0.8	dB
Return Loss — Input		IRL				dB
(Z _o = 75 Ohms)	40-200 MHz		20	_	_	
	200-600 MHz		19	_	_	
	600-870 MHz		18	_	_	
Return Loss — Output		ORL				dB
(Z _o = 75 Ohms)	40-200 MHz		20	_	_	
	200-600 MHz		19	_	_	
	600-870 MHz		18	_	_	



Table 3. Electrical Characteristics (V_{CC} = 24 Vdc, T_{C} = +30°C, 75 Ω system unless otherwise noted) (continued)

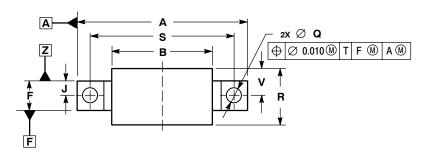
Characteristic		Symbol	Min	Тур	Max	Unit
Composite Second Order						dBc
(V _{out} = +44 dBmV/ch., Worst Case)	132-Channel FLAT	CSO ₁₃₂	_	-67	-60	
(V _{out} = +46 dBmV/ch., Worst Case)	112-Channel FLAT	CSO ₁₁₂		-65	-61	
$(V_{out} = +48 \text{ dBmV/ch.}, \text{Worst Case})$	79-Channel FLAT	CSO ₇₉	_	-72	-64	
Cross Modulation Distortion @ Ch 2						dBc
$(V_{out} = +44 \text{ dBmV/ch.}, FM = 55 \text{ MHz})$	132-Channel FLAT	XMD ₁₃₂	_	-58	-52	
$(V_{out} = +46 \text{ dBmV/ch.}, FM = 55 \text{ MHz})$	112-Channel FLAT	XMD ₁₁₂		-58	-52	
$(V_{out} = +48 \text{ dBmV/ch.}, FM = 55 \text{ MHz})$	79-Channel FLAT	XMD ₇₉	_	-58	-52	
Composite Triple Beat						dBc
(V _{out} = +44 dBmV/ch., Worst Case)	132-Channel FLAT	CTB ₁₃₂		-62	-58	
(Vout = +46 dBmV/ch., Worst Case)	112-Channel FLAT	CTB ₁₁₂		-61	-58	
(V _{out} = +48 dBmV/ch., Worst Case)	79-Channel FLAT	CTB ₇₉	_	-64	-60	
Noise Figure	50 MHz	NF	_	4.6	6.0	dB
	870 MHz		_	3.7	6.0	
DC Current (V_{DC} = 24 V, T_{C} = -20° to +100°C)	I _{DC}	230	250	265	mA

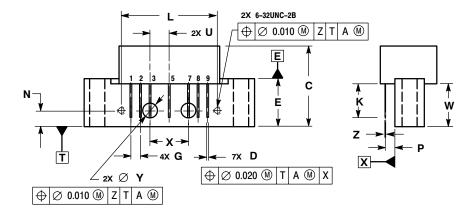
ARCHIVE INFORMATION



ARCHIVE INFORMATION

PACKAGE DIMENSIONS





- NOTES:
 1. DIMENSIONS ARE IN INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α		1.775		45.085	
В		1.085		27.559	
С		0.840		21.336	
D	0.015	0.021	0.381	0.533	
E	0.465	0.510	11.811	12.954	
F	0.300	0.325	7.62	8.255	
G	0.100	BSC	2.540 BSC		
J	0.156	BSC	3.962	BSC	
K	0.315	0.355	8.001	9.017	
L	1.000	BSC	25.400 BSC		
N	0.165 BSC		4.191 BSC		
P	0.100	BSC	2.540 BSC		
Q	0.148	0.168	3.759	4.267	
R		0.600		15.24	
S	1.500	BSC	38.100 BSC		
U	0.200	BSC	5.080 BSC		
V		0.250		6.350	
W	0.435		11.049		
Х	0.400 BSC		10.160 BSC		
Υ	0.152	0.163	3.861	4.140	
Z	0.009	0.011	0.229	0.279	

- STYLE 1:
 PIN 1. RF INPUT
 2. GROUND
 3. GROUND
 4. DELETED
 5. VDC
 6. DELETED
 7. GROUND
 8. GROUND
 9. RF OUTPUT

CASE 1302-01 ISSUE B



NX

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